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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. M122-2297		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Garo J. Derderian et al.			
					FILING DATE Filed Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
<i>mm</i>	AA	US2003/ 0026989 A1	Pub. 2/6/03	George et al.			07/16/02	
<i>mm</i>	AB	US2002/ 0137260 A1	Pub. 9/26/02	Leung et al.			01/11/01	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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EXAMINER <i>mm</i>			DATE CONSIDERED <i>6/19/2006</i>					
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MMS	AA	6,444,495 B1	09/02	Leung et al.			
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
MMS	AB		Frank, M. et al., "Enhanced Initial Growth of Atomic-Layer-Deposited Metal Oxides on Hydrogen-Terminated Silicon", App. Phys. Lett., Vol. 83, No. 4, July 28, 2003, pp. 740-742.				
S	AC		Rosidian, A. et al., "Formation of Ultrahard Metal Oxide Nanocluster Coatings at Room Temperature by Electrostatic Self-Assembly", SPIE Vol. 3675 (1999), pp. 113-119.				
S	AD		Sakaue, H. et al., "Conformable CVD of SiO ₂ into Deep Trench Using the Digital Method", Extended Abstracts of the 22nd (1990 International) Conf. on Solid State Devices and Materials, Sendai (1990), pp. 921-924.				
S	AE		Mountziaris, T. et al., "Gas-Phase and Surface Chemistry in Electronic Materials Processing", Materials Research Society Symposium Proceedings, Vol. 334, held 11/29/93 - 12/2/93, Boston, MA, pp. 1-36.				
S	AF		Perez, I. et al., "Fabrication and Characterization of 4H-SiC MOS Capacitors with Atomic Layer Deposited (ALD) SiO ₂ ", IEEE 7/00, pp. 144-147.				
S	AG		Sakaue, H. et al., "Digital Chemical Vapor Deposition of SiO ₂ Using a Repetitive Reaction of Triethylsilane/Hydrogen and Oxidation", JP Journal of App. Phys., Vol. 70, No. 1B, Jan. 1991, pp. L 124-L 127.				
S	AH		Klaus, J. et al., "Atomic Layer Deposition of SiO ₂ at Room Temperature Using NH ₃ -Catalyzed Sequential Surface Reactions", Surface Science 447 (2000), pp. 81-90.				
S	AI		Cameron, M. et al., "Atomic Layer Deposition of SiO ₂ and TiO ₂ in Alumina Tubular Membranes: Pore Reduction and Effect of Surface Species on Gas Transport", Langmuir 2000, 16, pp. 7435-7444.				
S	AJ		Horiike, Y. et al., "Filling of Si Oxide into a Deep Trench Using Digital CVD Method", App. Surface Science 46, (1990), pp. 168-174.				
MMS	AK		Wise, M. et al., "Dihydyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon", Mat. Res. Soc. Symp. Proc. Vol. 334, (© 1994 Materials Research Society), pp. 37-43.				
EXAMINER				DATE CONSIDERED			
MMS				6/19/2006			
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Sheet 1 of 1

Form PTO-1449U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO. M22-2287		SERIAL NO. 10728,328		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Gary J. Denderian et al.				
				FILING DATE: December 1, 2003		GROUP: Unknown		
U.S. PATENT DOCUMENTS								
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	AA							
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AM							
	AN							
	AO							
	AP							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
ms	AR	Klaus, J.W. et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions",						
ms		Surface Review and Letters, Vol. 6, Nos. 3 & 4 (1999), © World Scientific Pub. Co., pp. 435-448.						
	AS							
EXAMINER	DATE CONSIDERED		6/19/2006					
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PAGE 3/17 * RCVD AT 12/31/2003 12:01:24 PM [Eastern Standard Time] * SVR:USPTO-EFXXRF-1/2 * DNIS:8729306 * CSID:5098383424 * DURATION (mm-ss):06-12

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